IN THE UNITED STATES PATENT AND TRADEMARK OFFICE Filing Date ......August 30, 2000 Inventor ..... Jeffrey W. Honeycutt et al.

Assignee ..... Micron Technology, Inc. Group Art Unit ...... 2812

Examiner ..... Jennifer M. Kennedy Attorney's Docket No. ..... MI22-1332

Title: Methods of Forming Insulative Material Against Conductive Structures

## RESPONSE TO FEBRUARY 7, 2002 OFFICE ACTION

To:

Box Non-Fee Amendment

Assistant Commissioner for Patents

Washington, D.C. 20231

From:

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<u>AMENDMENTS</u>

APR 1 0 2002

In the Specification

TECHNOLOGY CENTER 2800

Replace the title with -- Methods of Forming Insulative Material Against Conductive Structures--

The paragraph beginning at p. 9, In. 8 is replaced with the following:

--In particular embodiments, one of layers 42 and 44 can consist of either  $\mathrm{Si_{z}O_{y}N_{z}}$  or  $\mathrm{Al_{p}O_{q}}$  (or consist essentially of such materials), and the other of layers

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